High Temperature Pt/Alumina Co-fired System for 500°C Electronic Packaging Applications

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Outline

- Background
  - 500°C SiC electronics and sensors
  - 96% alumina and thick-film metallization based packaging system for 500°C applications
  - Quick review of Au thick-film/alumina material systems
  - Challenges of thick-film/alumina systems

- Dielectric performance of selected HTCC alumina at high temperature
- Pt/alumina co-fired systems for high temperature applications
- Prototype 32-pin low power package and PCB
- Summary
Background

500°C SiC electronics and MEMS sensors have been demonstrated

- JFETs and JFETs based circuits demonstrated at NASA GRC
- MEMS based pressure sensors and Schottky diode based gas chemical sensors developed at NASA GRC
- Applications include aerospace engine control and long term Venus probes

96% alumina and thick-film metallization based prototype packaging system for 500°C SiC electronics and sensors

- 96% alumina provides acceptable electric/dielectric properties at high temperatures up to 550°C
- The system composed of chip-level package, printed circuit board (PCB), and edge-connector
Au thick-film and 96% alumina packaging system

Ceramic Chip-level Packages and PCBs

- Three types of ceramics and Au thick-film metallization based chip-level packages and printed circuit boards (PCBs)
- Chip-level packages characterized between room temperature and 500°C
- An edge connector in development for PCB – PCB (subsystem-level) interconnection
- 96% alumina provides best electrical performance at high temperatures

Chen and Hunter, 2005 HiTEN
Au thick-film 96% alumina packaging system

96% Alumina Chip-level Packages

Parasitic Capacitance and Conductance of Neighboring I/Os

<table>
<thead>
<tr>
<th>f (Hz)</th>
<th>T (°C)</th>
<th>T_R</th>
<th>100</th>
<th>150</th>
<th>200</th>
<th>250</th>
<th>300</th>
<th>350</th>
<th>400</th>
<th>450</th>
<th>500</th>
<th>550</th>
</tr>
</thead>
<tbody>
<tr>
<td>100</td>
<td>0.00nF</td>
<td>0.00nF</td>
<td>0.00nF</td>
<td>0.00nF</td>
<td>0.00nF</td>
<td>0.00nF</td>
<td>0.00nF</td>
<td>0.00nF</td>
<td>0.00nF</td>
<td>0.00nF</td>
<td>0.00nF</td>
<td>&lt; 5</td>
</tr>
<tr>
<td>120</td>
<td>0.5</td>
<td>0.5</td>
<td>0.5</td>
<td>0.5</td>
<td>0.5</td>
<td>0.5</td>
<td>0.5</td>
<td>0.5</td>
<td>0.5</td>
<td>0.5</td>
<td>0.5</td>
<td>5</td>
</tr>
<tr>
<td>1K</td>
<td>0.5</td>
<td>0.5</td>
<td>0.5</td>
<td>0.5</td>
<td>0.5</td>
<td>0.5</td>
<td>0.5</td>
<td>0.5</td>
<td>0.5</td>
<td>0.5</td>
<td>0.5</td>
<td>0.95</td>
</tr>
<tr>
<td>10K</td>
<td>0.49</td>
<td>0.50</td>
<td>0.50</td>
<td>0.49</td>
<td>0.50</td>
<td>0.50</td>
<td>0.50</td>
<td>0.50</td>
<td>0.50</td>
<td>0.50</td>
<td>0.50</td>
<td>0.50</td>
</tr>
<tr>
<td>100K</td>
<td>0.492</td>
<td>0.486</td>
<td>0.497</td>
<td>0.493</td>
<td>0.487</td>
<td>0.517</td>
<td>0.539</td>
<td>0.535</td>
<td>0.563</td>
<td>0.585</td>
<td>0.57</td>
<td></td>
</tr>
<tr>
<td>1M</td>
<td>0.501</td>
<td>0.497</td>
<td>0.485</td>
<td>0.506</td>
<td>0.499</td>
<td>0.529</td>
<td>0.533</td>
<td>0.55</td>
<td>0.556</td>
<td>0.544</td>
<td>0.55</td>
<td></td>
</tr>
</tbody>
</table>

Usable for packaging of many envisioned low power 500°C devices/circuits

> 50°C margin above 500°C

pF  μS
Au thick-film and 96% alumina packaging system

Static Thermal Test

- 96% alumina packaging system – chip-level packages and PCB
- less than 7% change in the JFET characteristics in first 6000 hours
- Tested at 500°C for over 10,000 hrs
- Demonstrated for long term operation at 500°C for the first time
Au thick-film/96% alumina system for pressure sensor packaging

Spark - Plug Type Package for High Temperature Capacitive Pressure Sensors

- 96% alumina substrate with Au thick-film metallization
- Four 10 mil diameter Au wires (I/Os) attached
- Au wires extended by four Pd wires
- Pd wires sealed in a commercial SS high temperature gland
- The gland operable up to 8000 psi
- Electrically characterized between RT and 500°C
- Low parasitic effects
- May apply to other micro-fabricated solid sensors

Chen, Beheim, Meredith, 2010 HiTEC
Spark-plug Type Package for High Temperature Capacitive Pressure Sensors

- Stainless steel sealing gland with LAVA seal
- Wiring configuration: two signal wires with third wire for “shield”
- Low parasitic capacitance at high frequencies > 10 kHz
- No direct impact on capacitance measurement results from parasitic conductance
- Usable for packaging some envisioned high temperature sensors
Spark-plug Type Package for High Temperature Capacitive Pressure Sensors

- Capacitive SiC pressure sensor with four polycrystalline SiC diaphragms electrically connected in parallel
- Measured at 100 kHz
- Packaging parasitic effects subtracted
- Parasitic conductance to be further reduced for packaging other sensors

Au thick-film/96% alumina system for pressure sensor packaging
HTCC Pt/Alumina for High Temperature Packaging

- **Au thick-film/96% alumina based packaging system**
  - Prototype package and PCB long-term tested at 500°C with SiC circuits
  - Packages assembled in a research lab – a non-mass-production step
  - Thermal dynamic stability issue of Au thick-film materials at elevated temperatures

- **High temperature co-fired (HTCC) alumina**
  - Co-fired at T >1500°C
  - A few percent of glass used in co-fired alumina systems
  - Dielectric performance at high temperatures tested
  - Pt metallization
    - Chemically stable at high temperatures
    - Low CTE (8.8x10^{-6}/C°)
    - Aluminum oxide for binder - Thermal dynamically stable
    - Alloy with Au, Au is always surface rich at elevated temperatures
Compared with 96% alumina:

- Dielectric constant of HTCC alumina is lower and increases less at 120Hz and 1kHz, compared with 96% alumina at low frequencies

Chen, 2012 HiTEC
Compared with 96% alumina:

- Dielectric constant of HTCC alumina is always lower and increases less with T at high frequencies

Chen, 2012 HiTEC
Compared with 96% alumina:

- Conductivity of HTCC alumina is ~ an order of magnitude lower compared with 96% alumina at temperatures above 300°C at the frequencies of 120Hz and 1kHz

Chen, 2012 HiTEC
Compared with 96% alumina:

- AC conductivity of HTCC alumina is always lower and increases less with T at 10kHz, 100kHz, and 1 MHz at T > 200°C

Chen, 2012 HiTEC
Compared with 96% alumina

- Dielectric constant of HTCC alumina is slightly lower and it increases less with temperature. AC conductivity of this material is also lower than that of 96% alumina at temperatures above 200°C
- Dissipation factor of HTCC alumina is always lower compared with that of 96% alumina at temperatures above 250°C
- HTCC alumina parts can be hermetic sealed
- Alumina based binders used for HTCC thick-film materials are expected to be thermal dynamically stable in a wide temperature range
Pt/HTCC Alumina Prototype Package

- Pt/HTCC alumina
- 32-IOs
- For low power circuits
- Via connecting pads
- 1 inch x 1 inch package
- Surface mount
- Preliminarily tested with SiC high temperature ICs
- In characterization/testing process
Pt/HTCC alumina PCBs, 2 inch x 2 inch, preliminarily tested with SiC circuits
Pt/HTCC Alumina Prototype Package and PCB

- SiC RAM decoder waveforms
- With 32-IOs HTCC package and PCB
- Initial test data recorded at 501°C

- SiC D/A convertor
- With 32-IOs HTCC package and PCB
- Initial test data recorded at 500°C

G.W. Hunter, P.G. Neudeck, D.J. Spry, G.E. Ponchak, G.M. Beheim et al, Venus Science Priorities for Laboratory Measurements Workshop, April, 2015, Hampton, VA.
Summary

96% alumina substrate and thick-film metallization based packaging systems demonstrated at 500°C
- Au thick-film/alumina chip-level packages and PCBs
- Static thermal test of packaged SiC JFET circuits successfully at 500°C for over 10,000 hours
- Thermal dynamic stability issue of thick-film binders at elevated temperatures
- Laboratory step involved on package assemble
  - Chip - level packages not fully commercially fabricated

Pt/HTCC alumina system
- Dielectric properties of selected HTCC alumina tested up to 550°C
- Better dielectric performance
- Co-fire process more suitable for large scale commercialization
- Alumina binder for Pt metallization more stable at high temperatures
- Dielectric performance of 32-IOs co-fired packages in evaluation
- Prototype package initially tested with SiC circuits at 500°C
- Further development needed
Thank You Very Much for Your Attention!

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